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United States Patent [19]

Lee et al.

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[54]	FET WITH	GATE SPACER
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[22]	Filed:	Oct. 17, 1989
[51]	Int. Cl.5	H01L 21/24; H01L 21/265;
[En]	II.C. CI	H01L 21/336
[52]	U.S. CI	
[58]	Field of Search	
[56]		References Cited

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[57] ABSTRACT

A semiconductor integrated circuit structure and method of fabrication is disclosed. The structure includes a FET gate with adajcent double or triple-layered gate spacers. The spacers permit precise tailoring of lightly doped drain junction profiles having deep and shallow junction portions. In addition, a self-aligned silicide may be formed solely over the deep junction portion thus producing a reliable low contact resistance connection to source and drain.

FOREIGN PATENT DOCUMENTS

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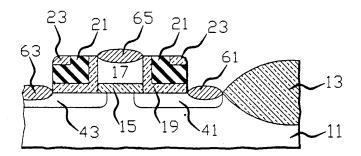
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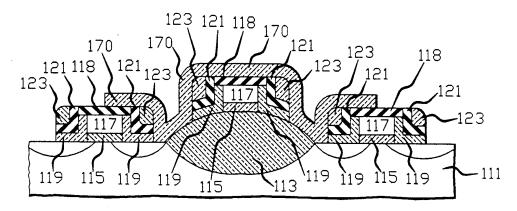
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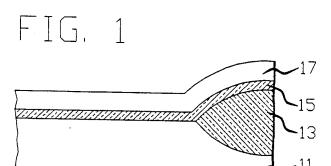
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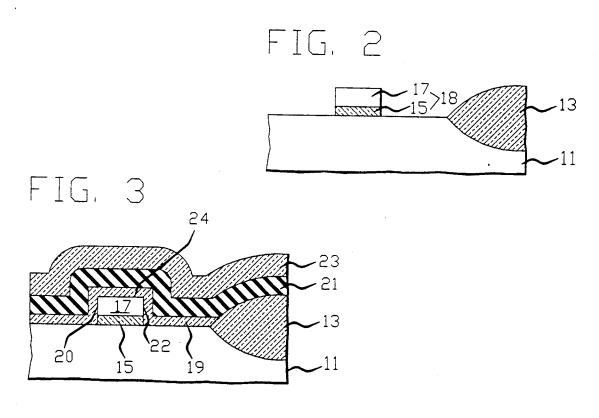
5 Claims, 5 Drawing Sheets

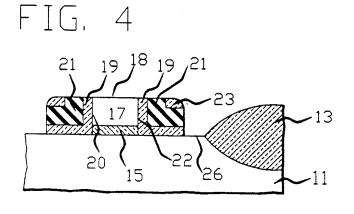


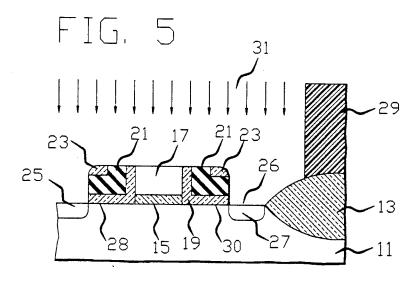












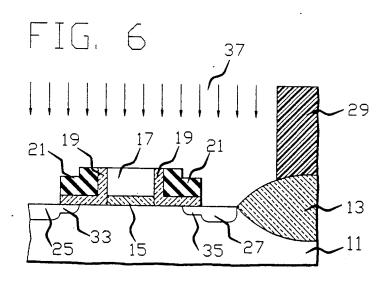


FIG. 7

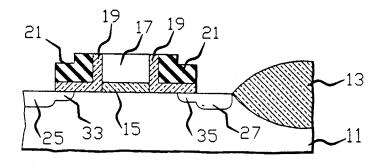




FIG. 8

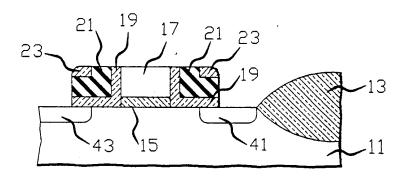


FIG. 9

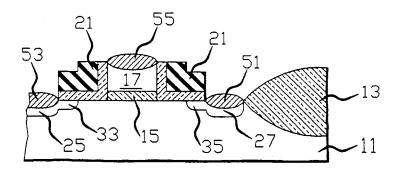


FIG. 10

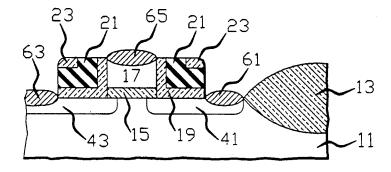




FIG. 11

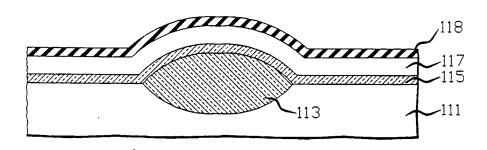


FIG. 12

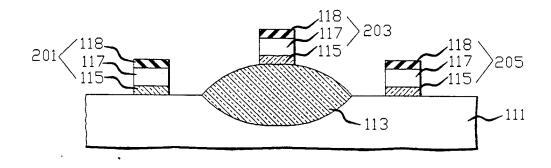
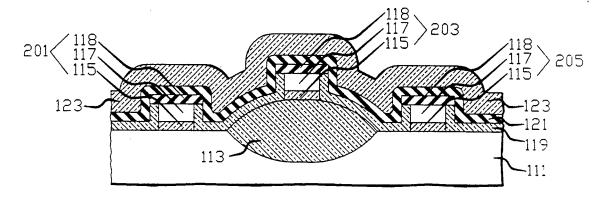


FIG. 13





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